

BACK-END

MOS-FET

IGBT

DIODE

SWITCHING TIME TEST SYSTEM スイッチングタイムテストシステム

SWS1530ZZ

1500V
999A3000A
(Short Circuit)

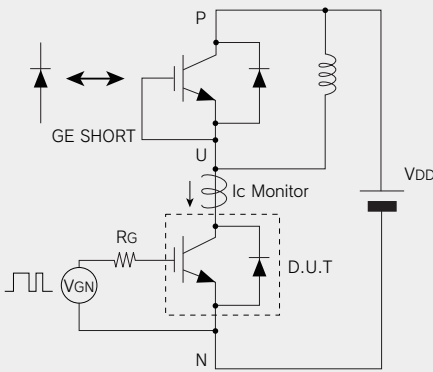
NEW

- SWS1530ZZ has been designed to test short circuit tolerance and switching characteristics of IGBT, MOS-FET and DIODE. It is possible to test automatically with temperature environment of $-40^{\circ}\text{C} \sim 175^{\circ}\text{C}$, and from low breakdown voltage to high breakdown voltage area.
- SWS1530ZZは、IGBT、MOS-FET、ダイオードのスイッチング特性、及び短絡耐量を測定する装置です。低耐圧より高耐圧領域、また、温度環境 $-40^{\circ}\text{C} \sim 175^{\circ}\text{C}$ まで自動で測定可能です。

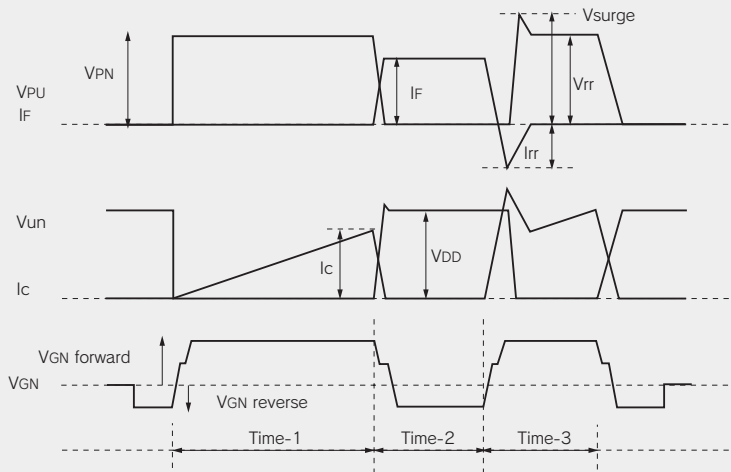


Note) The equipment of the left side in a picture (Temperature environmental system) is an option.
注) 写真左側の装置 (温度環境試験器) はオプション品です。

Fundamental Test Circuit (L-LOAD Switching)



Measurement Waveform (L-LOAD Switching)



MODEL

SWS1530ZZ

TEST ITEMS

L-LOAD/R-LOAD SWITCHING	$I_c(I_D)$, $t_d(\text{on})$, t_r , $t_d(\text{off})$, t_f , $e(\text{on})$, $e(\text{off})$
di/dt	I_{rr} , t_{rr} , Q_{rr} , di/dt , dir/dt , V_{dsurge}
AVALANCHE	I_{ava} , V_{ava} , E_{ava} , V_{surge}
QG	Q_{gs} , Q_{gd} , Q_g , V_{th}
SHORT CIRCUIT ASO	V_{sc} , I_{sc} , V_{surge} , E_{sc}

SETTING RANGE

MEASURABLE DEVICE	IGBT, MOS-FET, DIODE
MEASUREMENT RANGE	000.0ns~999.9 μ s
VDD	0020V~1500V 1V STEP
ID (limit)	0001A~3000A 1A STEP
VGF/VGR	$\pm 00.0\text{V} \sim \pm 30.0\text{V}$ 0.1V STEP
Ig	To choose from 0.1mA, 1mA and 10mA
Time-1	0000.0 μ s~9999.9 μ s 0.1 μ s STEP
Time-2	000.0 μ s~999.9 μ s 0.1 μ s STEP
Time-3	00.0 μ s~99.9 μ s 0.1 μ s STEP
Time-4	0000 μ s~9999 μ s 1 μ s STEP

BINNING

OPEN/SHORT CHECK	Vg ON : $V_{CE} \geq 10\text{V} \dots \text{OPEN}$ Vg OFF : $V_{CE} \leq 1/2 V_{DD} \dots \text{SHORT}$
BIN INDICATION	ERROR, PASS, LIMIT-FAIL, OPEN, SHORT

DIMENSIONS & WEIGHT

MAIN UNIT	550(W)×860(D)×1700(H)···185kg
MEASUREMENT UNIT	1100(W)×1130(D)×1850(H)···385kg